

SEMICONDUCTOR LIGHT EMITTING ELEMENT, SEMICONDUCTOR LIGHT EMITTING DEVICE AND MANUFACTURE THEREOF

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- international: H01L33/00; H01L33/00; (IPC1-7): H01L33/00; H01S3/18
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Abstract of JP11087778
PROBLEM TO BE SOLVED: To make a light emission wavelength stable and allow light emission with high brightness in a wavelength in a region from visible right to infrared rays. SOLUTION: A fluorescent substance is included or deposited in any part of the semiconductor light emitting element 10. The fluorescent substance has an absorption peak in a wavelength band of 340 to 380 nm. Therefore, in order to effectively convert wavelength by the fluorescent substance, a light emitting layer 20 desirably emits ultraviolet rays of a wavelength band of 308 nm or less. A site to include the fluorescent substance in the semiconductor element 10 may be a p-side electrode layer 26, first. Then, a silicon oxide layer 45 or a current preventing layer 30 may follow. Alternatively any of respective semiconductor layers 14 to 24 may follow. A substrate 12 may follow further.

